

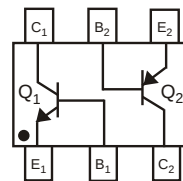
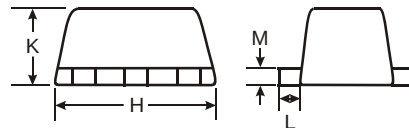
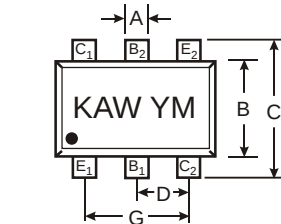
COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Σ Epitaxial Die Construction
- Σ Two internally isolated NPN/PNP Transistors in one package
- Σ Ultra-Small Surface Mount Package
- Σ **Lead Free By Design/RoHS Compliant (Note 2)**
- Σ "Green" Device (Note 3)

Mechanical Data

- Σ Case: SOT-563
- Σ Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Σ Moisture Sensitivity: Level 1 per J-STD-020C
- Σ Terminals: Finish æ Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Σ Terminal Connections: See Diagram
- Σ Marking (See Page 3): KAW
- Σ Ordering & Date Code Information: See Page 4
- Σ Weight: 0.003 grams (approximate)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	æ
All Dimensions in mm			

Maximum Ratings @ T_A = 25°C unless otherwise specified **NPN, BC847B Type (Q₁)**

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA

Maximum Ratings @ T_A = 25°C unless otherwise specified **PNP, BC857B Type (Q₂)**

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1) @ T _A = 25°C Total Device	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1) @ T _A = 25°C	R _{qJA}	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Characteristic (Note 4)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\text{mA}$, $I_B = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 1\text{mA}$, $I_C = 0$
DC Current Gain	h_{FE}	200	290	450	—	$V_{CE} = 5.0\text{V}$, $I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	90 200	250 600	mV	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$ $I_C = 100\text{mA}$, $I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	700 900	—	mV	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$ $I_C = 100\text{mA}$, $I_B = 5.0\text{mA}$
Base-Emitter Voltage	$V_{BE(ON)}$	580 —	660 —	700 720	mV	$V_{CE} = 5.0\text{V}$, $I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}$, $I_C = 10\text{mA}$
Collector-Cutoff Current	I_{CBO}	— —	— —	15 5.0	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}$, $T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	300	—	MHz	$V_{CE} = 5.0\text{V}$, $I_C = 10\text{mA}$, $f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3.5	6.0	pF	$V_{CB} = 10\text{V}$, $f = 1.0\text{MHz}$

Note: 4. Short duration pulse test used to minimize self-heating effect.

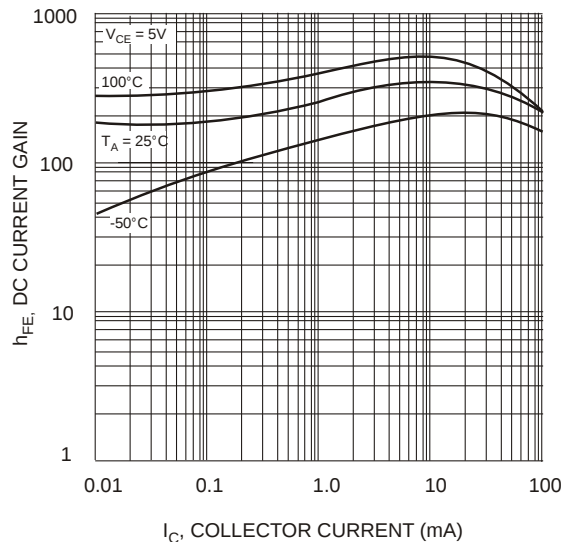


Fig. 1, DC Current Gain vs Collector Current (BC847B Type)

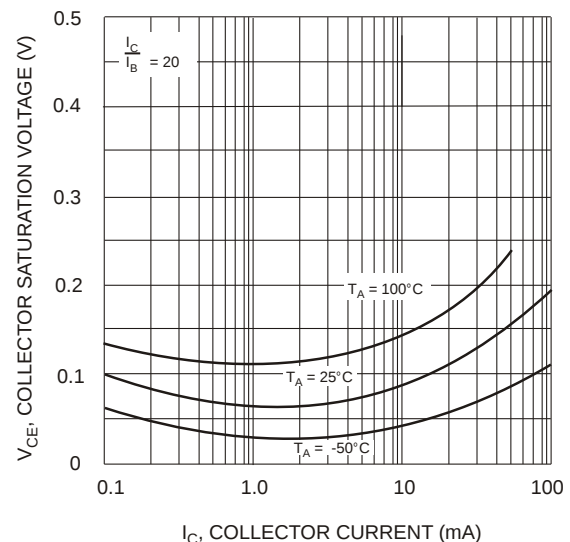


Fig. 2, Collector-Emitter Saturation Voltage vs Collector Current (BC847B Type)

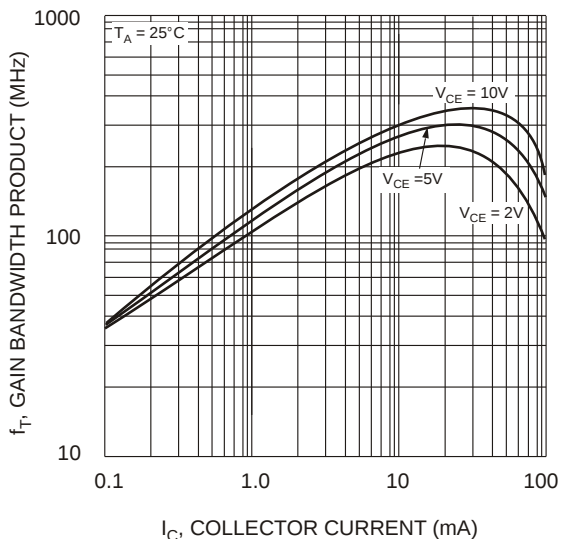


Fig. 3, Gain Bandwidth Product vs Collector Current (BC847B Type)

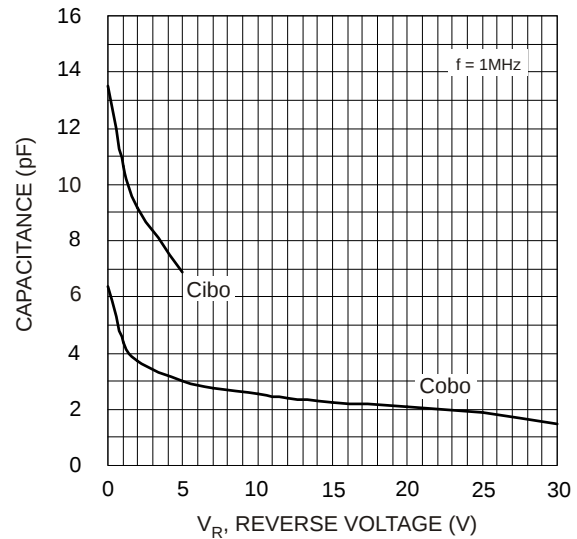


Fig. 4, Capacitance vs. Reverse Voltage (BC847B Type)

Characteristic (Note 5)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50	—	—	V	$I_C = -10\text{mA}$, $I_B = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-45	—	—	V	$I_C = -10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -1\text{mA}$, $I_C = 0$
DC Current Gain	h_{FE}	220	290	475	—	$V_{CE} = -5.0\text{V}$, $I_C = -2.0\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-75 -250	-300 -650	mV	$I_C = -10\text{mA}$, $I_B = -0.5\text{mA}$ $I_C = -100\text{mA}$, $I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-700 -850	— -950	mV	$I_C = -10\text{mA}$, $I_B = -0.5\text{mA}$ $I_C = -100\text{mA}$, $I_B = -5.0\text{mA}$
Base-Emitter Voltage	$V_{BE(ON)}$	-600 —	-650 —	-750 -820	mV	$V_{CE} = -5.0\text{V}$, $I_C = -2.0\text{mA}$ $V_{CE} = -5.0\text{V}$, $I_C = -10\text{mA}$
Collector-Cutoff Current	I_{CBO}	— —	— —	-15 -4.0	nA μA	$V_{CB} = -30\text{V}$ $V_{CB} = -30\text{V}$, $T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	200	—	MHz	$V_{CE} = -5.0\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3	4.5	pF	$V_{CB} = -10\text{V}$, $f = 1.0\text{MHz}$

Note: 5. Short duration pulse test used to minimize self-heating effect.

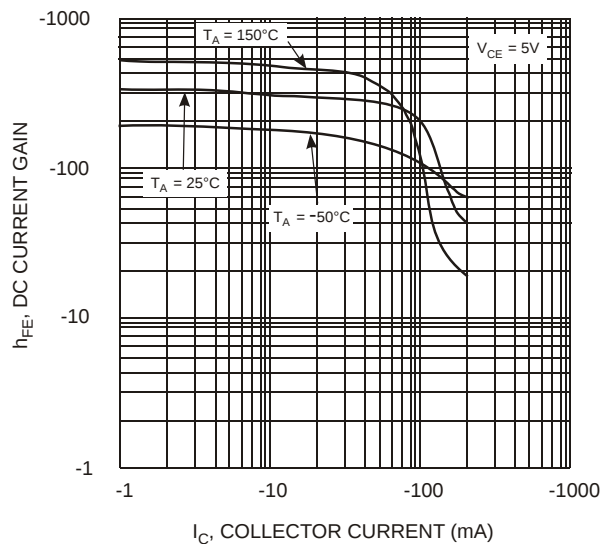


Fig. 5, DC Current Gain vs. Collector Current (BC857B Type)

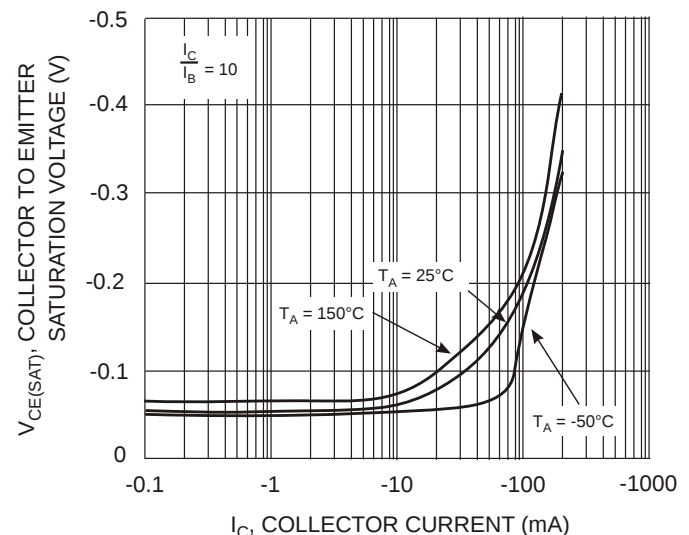


Fig. 6, Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

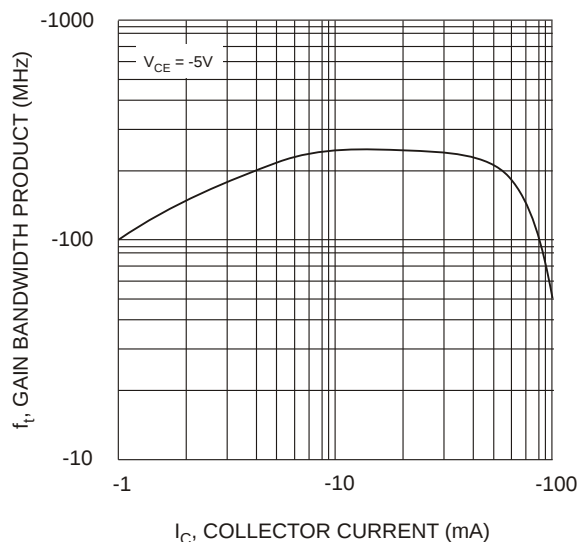


Fig. 7, Gain Bandwidth Product vs. Collector Current (BC857B Type)

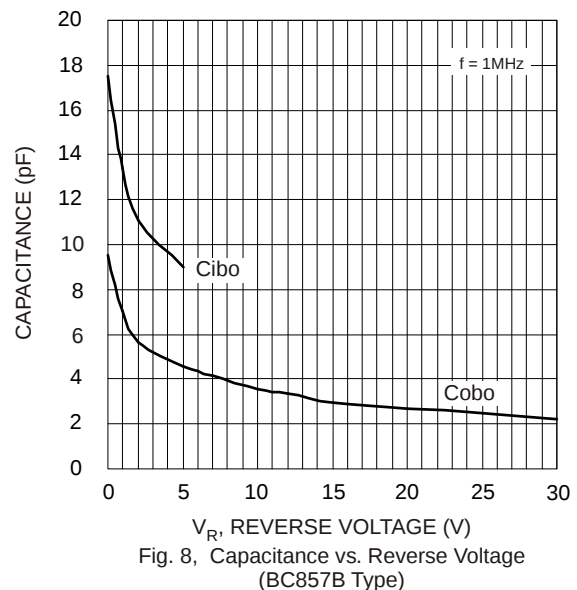
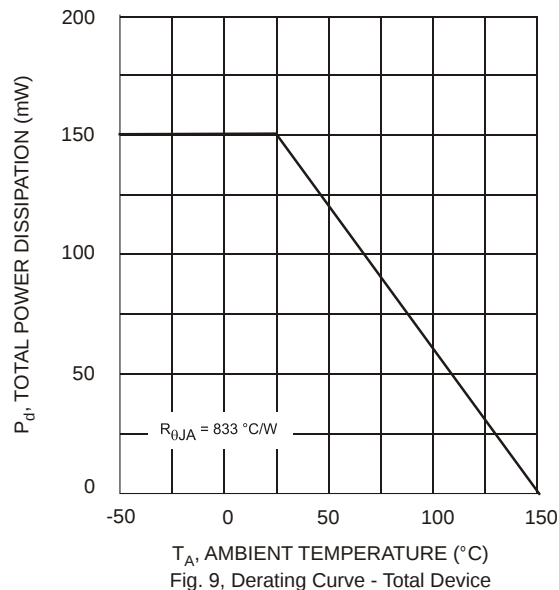


Fig. 8, Capacitance vs. Reverse Voltage (BC857B Type)

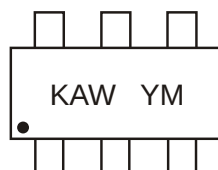


Ordering Information (Note 6)

Device	Packaging	Shipping
BC847BVN-7	SOT-563	3000/Tape & Reel

Notes: 6. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



KAW = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: R = 2004
 M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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